L Number	Hits	Search Text	DB	Time stamp
-	1	("4954744").PN.	USPAT; US-PGPUB	2003/11/07 11:06
-	10	((insulating insulation) adj (layer film coating)) with (metal adj oxide adj particle)	USPAT; US-PGPUB	2002/11/07 10:58
-	3	((insulating insulation) adj (layer film coating)) with (metal adj oxide adj particle) and MIM	USPAT; US-PGPUB	2002/11/07 10:57
-	0	((insulating insulation) adj (layer film coating)) with (sno2 adj particle) and substrate	USPAT; US-PGPUB	2002/11/07 10:59
-	2364	substrate and (((insultating dielectric (metal adj oxide)) adj (layer film coating)) same particle)	USPAT; US-PGPUB	2002/11/07 11:04
-	131615	(insulating dielectric (metal adj oxide)) adj (layer film coating)	USPAT; US-PGPUB	2002/11/07 11:06
-	2331	(substrate and (((insultating dielectric (metal adj oxide)) adj (layer film coating)) same particle)) and substrate	USPAT; US-PGPUB	2002/11/07 11:08
-	3	(((insulating dielectric (metal adj oxide)) adj (layer film coating)) with ((metal adj oxide adj particle) ((SnO2) adj particle))) and substrate	USPAT; US-PGPUB	2002/11/07 11:09
-	5	((insulating dielectric (metal adj oxide)) adj (layer film coating)) with ((metal adj oxide adj particle) ((SnO2) adj particle))	USPAT; US-PGPUB	2002/11/07 11:18
-	0	(electron adj emitting adj device).ti. and (metal adj oxide adj particle)	USPAT; US-PGPUB	2002/11/07 11:19
-	0	(electron adj emitting).ti. and (metal adj oxide adj particle)	USPAT; US-PGPUB	2002/11/07 11:19
-	23	(anode adj segments) and register and voltage and display	USPAT; US-PGPUB	2002/11/07 12:28
-	3	"6124676"	USPAT; US-PGPUB	2002/11/07 15:06
-	14	("3892998" | "4088925" | "4575721" | "4650434" | "5030888" | "5045846" | "5066890" | "5075597" | "5086257" | "5237315" | "5519520" | "5674553" | "5834891" | "5867135").PN.	USPAT	2002/11/07 14:22
-	14	("3892998" | "4088925" | "4575721" | "4650434" | "5030888" | "5045846" | "5066890" | "5075597" | "5086257" | "5237315" | "5519520" | "5674553" | "5834891" | "5867135").PN.	USPAT	2002/11/07 14:23
-	0	(vinyl adj ink) with (uv adj curable adj ink)	USPAT; US-PGPUB	2002/11/07 15:07
-	0	(vinyl adj ink) with (uv adj curable adj ink)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:08
-	0	(vinyl adj ink) same (uv adj curable adj ink)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:08
-	2	(vinyl adj ink) and (uv adj curable adj ink)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:10
-	0	(vinyl adj ink) with (uv adj curable)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:10
-	0	(vinyl adj ink) with (uv adj cur)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:10
-	5	(vinyl adj ink) and (uv adj curable)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:19

-	0	(electronic adj grade adj vinyl adj ink) with UV	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:20
-	6	(electronic adj grade adj vinyl adj ink)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:26
-	379	uv adj curable adj ink	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:26
-	170	uv adj curable adj ink	USPAT	2002/11/07 15:27
-	0	(electron adj emitting adj device) and (sio2 adj layer) and (particle adj size)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/19 11:16
-	53	(electron adj emitting adj device) and (particle adj size) and nm	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/19 11:30
-	19	(electron adj emitting adj device) and substrate and ((Sio2 (silicon adj dioxide)) adj (layer coating film))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/19 11:42
-	56	(substrate with sodium) and (metal adj oxide adj layer)	USPAT; US-PGPUB	2002/11/19 11:48
-	55	"4954744"	USPAT; US-PGPUB	2002/11/19 12:15
-	2	substrate and (sodium adj blocking adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/19 12:18
-	4	substrate and (antistatic adj layer) and (electron adj emitting)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/19 13:55
-	0	conventinal adj pixel adj shaped adj pattern	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/19 13:56
-	1	pixel adj shaped adj pattern	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/19 13:56
-	10	"5532544"	USPAT; US-PGPUB	2002/11/22 16:28
-	1	("4954744").PN.	USPAT; US-PGPUB	2002/11/22 16:31
-	3	(antistatic adj layer) with (silicon adj dioxide)	USPAT	2002/11/22 16:34
-	0	(antistatic adj layer) Near (silicon adj dioxide)	USPAT	2002/11/22 16:32
-	3	(antistatic adj layer) with (silicon adj dioxide, SiO)	USPAT	2002/11/22 16:35
-	10	(antistatic adj layer) with (silicon adj dioxide, SiO, MgO)	USPAT	2002/11/22 17:39
-	95	(electron adj emitting adj device).ti.	USPAT	2002/11/22 17:40
-	2	(electron adj (emission emissive))and substrate and (metal adj oxide adj particle) and sodium and diffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/07 11:10
-	2	(electron adj (emission emissive))and substrate and (metal adj oxide adj particle)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/07 11:10
-	1444	(electron adj (emission emissive))and substrate and (particle)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/07 11:11

-	7	(electron adj (emission emissive))and (metal adj oxide adj particle)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/07 11:12
-	339	(surface adj conduction)and (electron adj emission) and particle	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/07 12:25
-	134658	substrate with (((insulating dielectric) layer)and (metal oxide adj particle))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/07 12:27
-	31	substrate with (((insulating dielectric) layer)and (metal adj oxide adj particle))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/07 12:32
-	682	substrate with (((insulating dielectric) layer)and (metal Near3 particle))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/07 12:37
-	229	(313/309-310, 313/351, 313/336, 313/495-496).ccls. and metal and particle and substrate and ((insulating dielectric) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/07 12:42
-	24	((315/169.1,169)(345/74)).ccls.and particle and substrate and ((insulating dielectric) adj layer)	USPAT; US-PGPUB	2003/11/07 12:44